



$V_{GS}=4.5V$ 9.5 m
44 A

Part Number Marking
HGA093N12SL GA093N12SL

Absolute Maximum Ratings at $T_J=25^{\circ}C$ (unless otherwise specified)

	Symbol	Conditions	Value	
Continuous Drain Current (Silicon Limited)	I_D	$T_C=25^{\circ}C$	44	A
		$T_C=100^{\circ}C$	31	
Drain to Source Voltage	V_{DS}	-	120	V
Gate to Source Voltage				
Pulsed Drain Current		-	250	
Avalanche Energy, Single Pulse				
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-Ambient	R_{JA}	65	$^{\circ}C/W$
Thermal Resistance Junction-Case	R_{JC}		$^{\circ}C/W$

Gate Resistance	R_G	$V_{DS}=5V, I_{D1}$ $V_{GS}=0V, V_{DS}$ Open, $f=1MHz$	-	70	-	S
			-	1	-	
Input Capacitance	C_{iss}		-	2626	-	
Output Capacitance	C_{oss}	$V_{GS}=0V, V_{DS}=60V, f=1MHz$	-	329	-	pF
	C_{riss}		-	11	-	
Total Gate Charge	$Q_g(10V)$		-	38	-	
Total Gate Charge	$Q_g(4.5V)$		-	18	-	
Gate to Source Charge	Q_{gs}	$V_{DD}=60V, I_D=20A, V_{GS}=10V$	-	7	-	nC
Gate to Drain (Miller) Charge	Q_{gd}		-	5	-	
Turn on Delay Time	$t_{d(on)}$		-	13	-	
Rise time	t_r	$V_{DD}=60V, I_D=20A, V_{GS}=10V,$	-	7	-	ns
Turn off Delay Time	$t_{d(off)}$	$R_G=10 \Omega$	-	22	-	
Fall Time	t_f		-	9	-	
Reverse Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}		-	53	-	ns
Reverse Recovery Charge	Q_{rr}	$V_R=60V, I_F=20A, di_F/dt=100A/\mu s$	-	58	-	nC

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

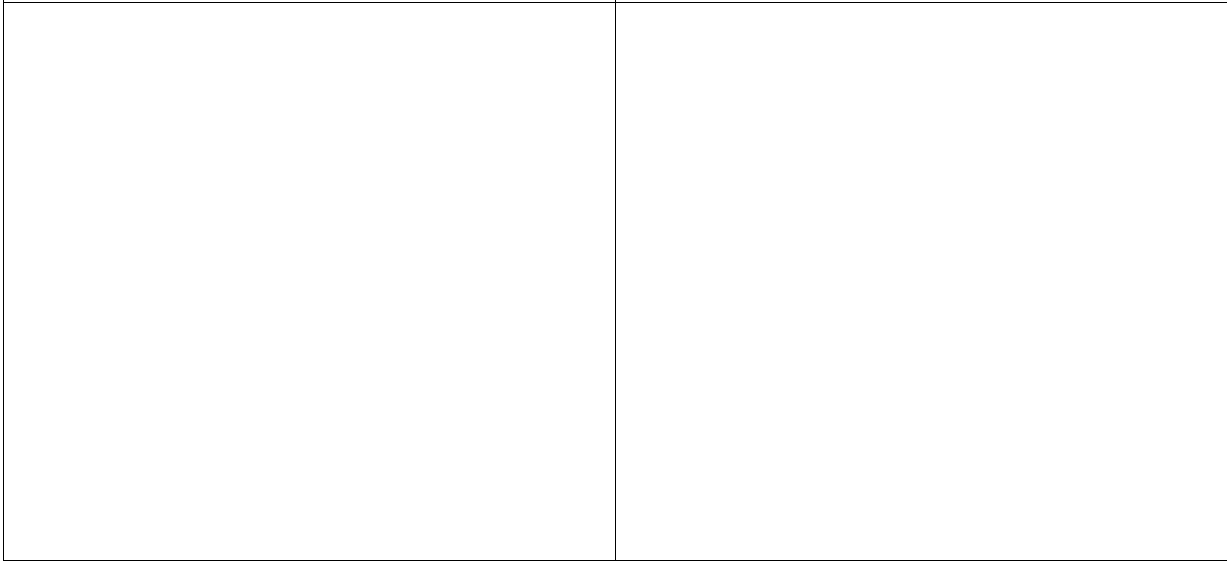


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

Figure 4. Normalized On-Resistance vs. Junction Temperature

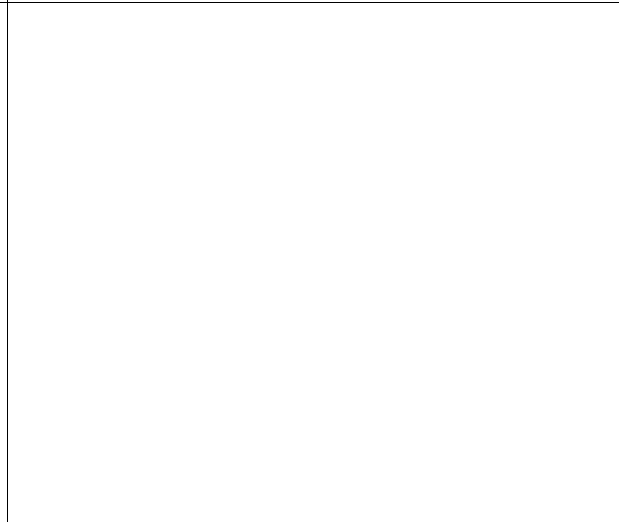
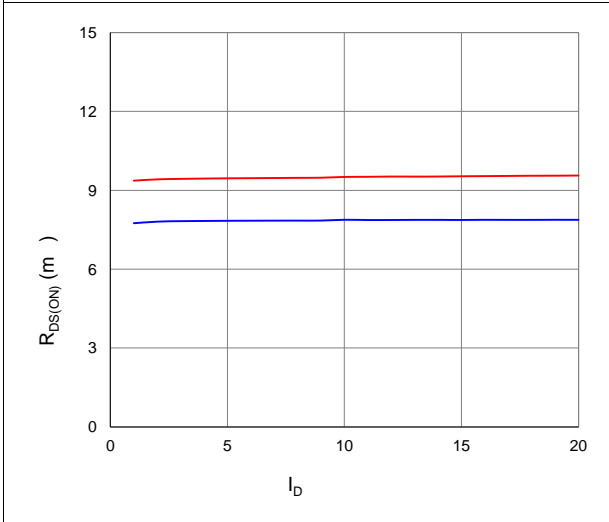


Figure 5. Typical Transfer Characteristics

Figure 6. Typical Source-Drain Diode Forward Voltage

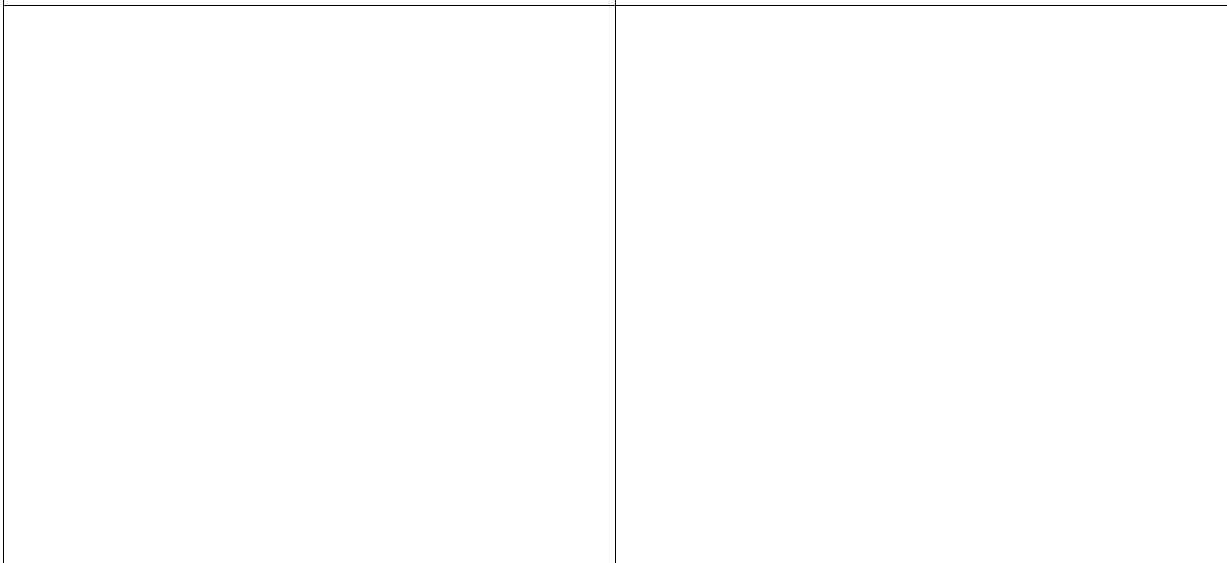


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

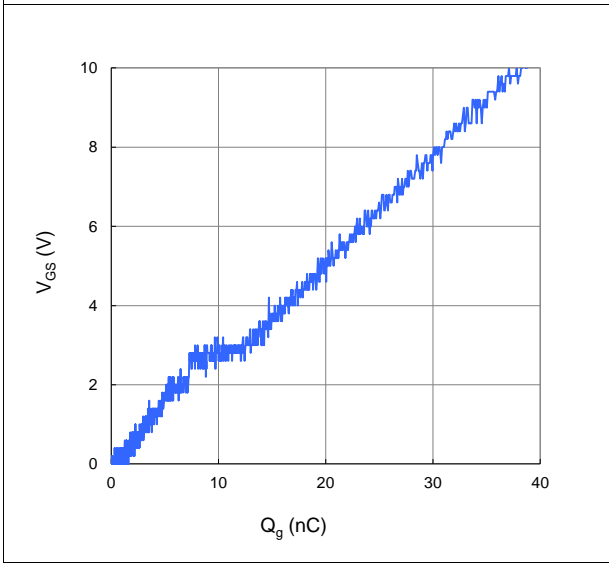


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

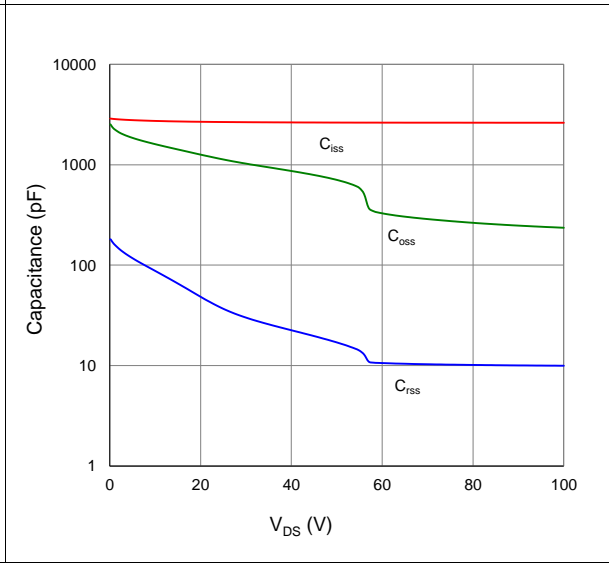


Figure 9. Maximum Safe Operating Area

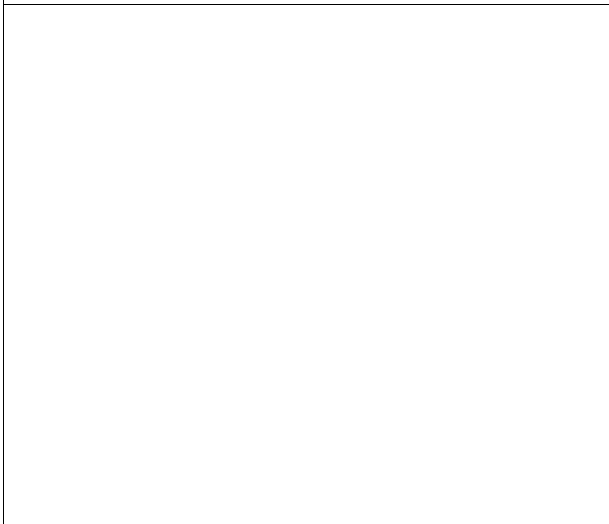


Figure 10. Maximum Drain Current vs. Case Temperature

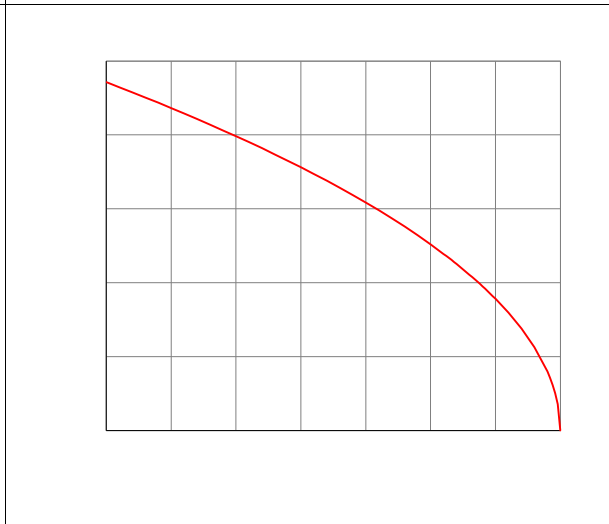
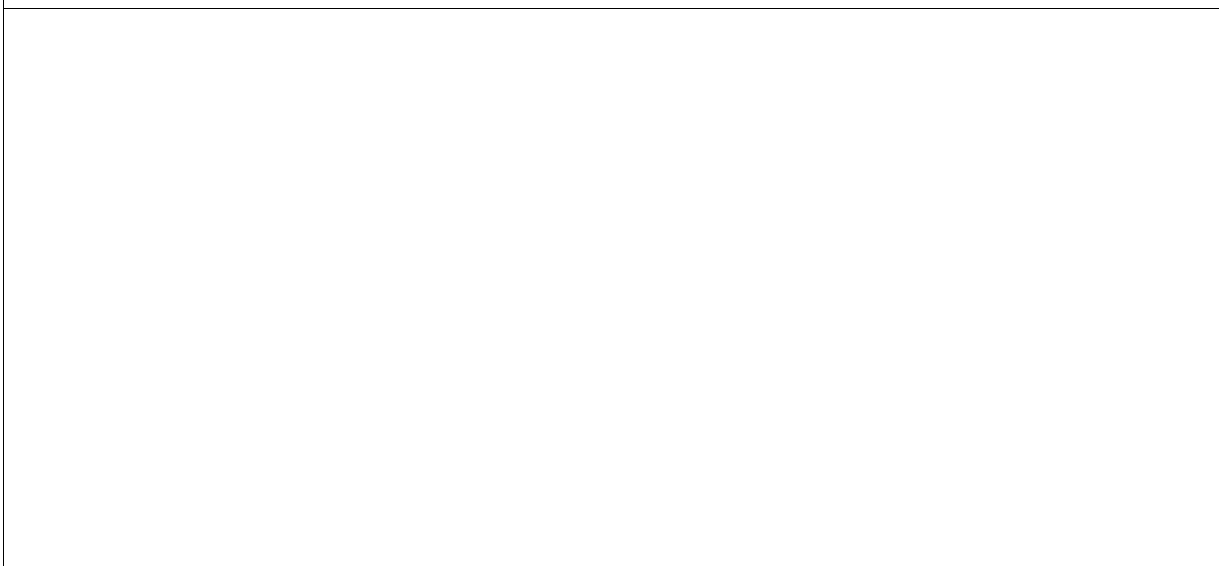
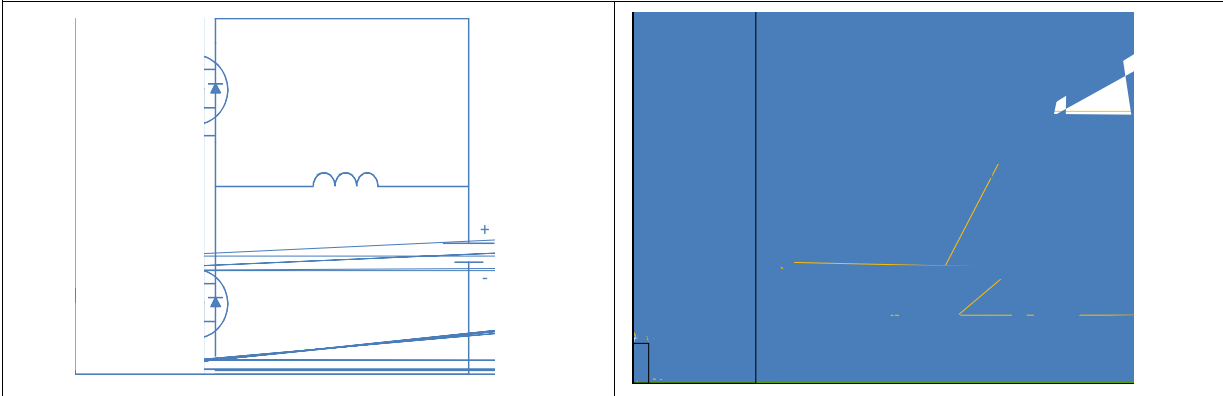


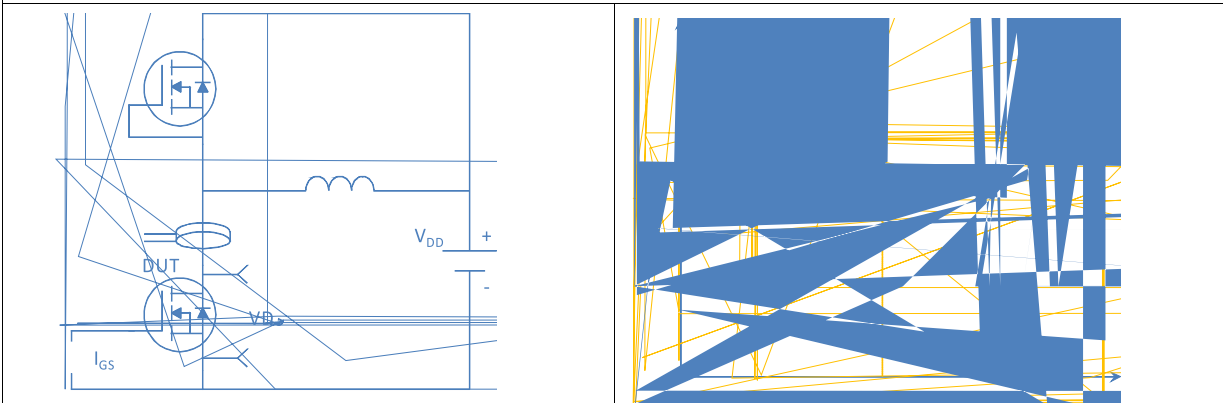
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



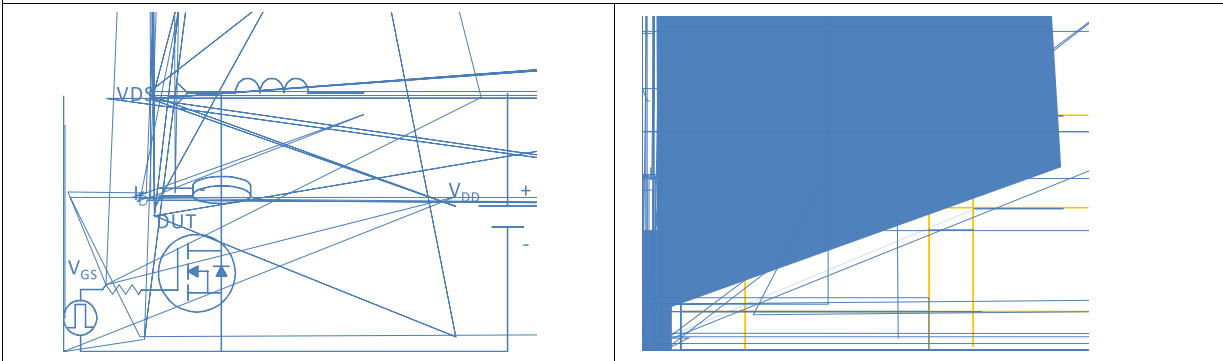
Inductive switching Test



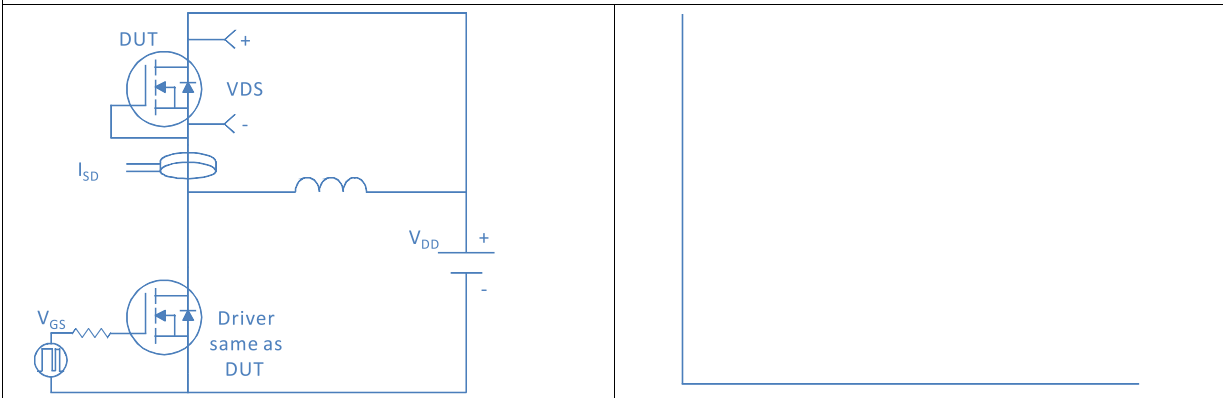
Gate Charge Test

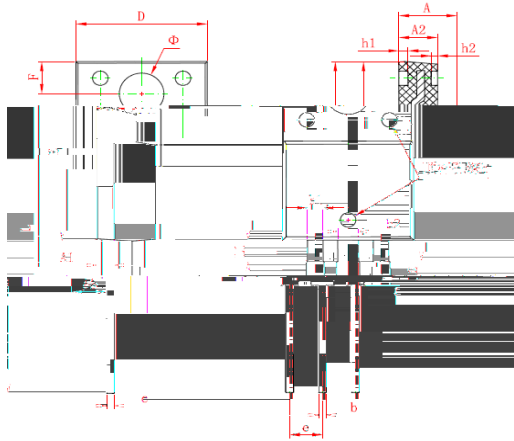


Uclamped Inductive Switching (UIS) Test



Diode Recovery Test



Package Outline
TO-220F, 3 leads


Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	0.400	0.500	0.016	0.020
a	0.400	0.500	0.016	0.020
b1	1.100	1.300	0.043	0.051
b	0.400	0.500	0.016	0.020
c	0.400	0.500	0.016	0.020
e	0.400	0.500	0.016	0.020
D	0.012	0.000	0.000	0.000
E	0.012	0.000	0.000	0.000
h1	1.118	28.000	28.400	1.102
h2	0.375	1.700	1.500	0.067
1.1	0.083	1.900	2.100	0.075